

Abstracts

RF Silicon MOS Integrated Power Amplifier for Analog Cellular Applications

D. Ngo, C. Dragon, J. Costa, D. Lamey, E. Spears, W. Burger and N. Camilleri. "RF Silicon MOS Integrated Power Amplifier for Analog Cellular Applications." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 559-562.

We report the RF performance of the first Integrated Power Amplifier using silicon MOS Field Effect Transistors, shunt and series capacitors, transmission lines, spiral inductors, ground vias and ESD protection devices. The amplifier provided an output power of 1.5W and 56% efficiency at a supply voltage of 5.8V (850MHz) with 25dB of small signal gain and more than 10dB input return loss.

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